YUAN-CHUN LUO

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RESEARCH INTEREST

Carbon nanotube, 2D Materials, and energy-efficient transistors

EDUCATION

National Tsing Hua University (NTHU), Hsinchu, Taiwan

Sep. 2014 - Jun. 2018

B.S., Electrical Engineering (EE)

Overall GPA: 4.07/4.3 (3.93/4)

RESEARCH EXPERIENCE

Purdue University - ALD Group

Visiting Student

West Lafayette, IN Oct. 2018 - present

- · Advisor: Professor Peide(Peter) Ye
- · Apply germanium ferroelectric nanowire FETs as analog memories.

National Chiao Tung University (NCTU), DSML Group

Hsinchu, Taiwan Jan. 2017 - Sep. 2018

Research Assistant

· Advisor: Professor Steve S. Chung

- · Measured internal voltage, extract negative capacitance(NC) values and free energy, and minimize hysteresis in Ferroelectric FETs (SSDM'18).
- · Built C++ codes to analyze data from measurement more efficiently.
- · Verified RF characteristics for FinFETs using the simulation tool, TCAD.

NTHU - THz Optoelectronic Devices Lab

Research Assistant

Hsinchu, Taiwan Jun. 2017 - Jun. 2018

- · Advisor: Professor Shang-Hua Yang
- · Designed THz optoelectronic photomixers using COMSOL Multiphysics.
- · Analyzed beam steering in antenna arrays using Matlab.

NTHU - SSD LAB

Research Assistant

Hsinchu, Taiwan

Sep. 2016 - Aug. 2017

- · Advisor: Professor Ren-Shuo Liu.
- · Achieved run-time power-accuracy tunability for low-cost and adaptive Convolutional Neural Networks using Python (VLSI-DAT'18).

PUBLICATION

An Experimental Method of Negative Capacitance(NC) Extraction in NC-gated-FinFET and Obtainment of near-free-Hysteresis Characteristics by Body Effects

· Y.-C. Luo, E. R. Hsieh, C. J. Su, Steve S. Chung, T. P. Chen, S. A. Huang, T. J. Chen, and Osbert Cheng; Applied Physics Letter (In preparation)

New Experimental Approaches to Extracting Negative Capacitances of 14nm NC-FinFET in Exploration of Short-channel & Body Effect to Achieve Free Hysteresis.

· Y.-C. Luo, E. R. Hsieh, C. J. Su, Steve S. Chung, T. P. Chen, S. A. Huang, T. J. Chen, and Osbert Cheng; 2018 SSDM Late News (Accepted)

DrowsyNET: Convolutional Neural Networks with Runtime Power-Accuracy Tunability Using Inference-Stage Dropout.

· R.-S. Liu, Y.-C. Lo, Y.-C. Luo, Chih-Yu Shen, and Cheng-Ju Lee; 2018 VLSI-DAT (Accepted)

SELECTED HONOR AND AWARD

Champion, Contest of implementation with more than 100 student competitors. EE, NTHU, 2018

Runner up, Contest of implementation with more than 250 student competitors. EECS, NTHU, 2018

Excellent-EECS student award for top 10% of all students. EECS, NTHU, 2017

Oversea exchange student scholarship with USD 3100. EE, NTHU, 2016

Outstanding academic achievement for top 5% of all students. EE, NTHU, 2015

LEADERSHIP & TEAMWORK

President, Student Association

EE, NTHU

Jun. 2016 - Jun. 2017

- · Built a 20-student team to receive students and an advisor from City University of Hong Kong.
- · Arranged undergraduate-project contests with six professors as judges for over 100 student participants.
- · Organized Christmas party for more than 200 students from four different departments.

RELEVANT COURSES

Core Courses

ULSI Technology (A+, graduate level, nano-fabrication) Semiconductor Microwave Devices (A+, graduate level) Introduction to Solid-State Physics (A+) Introduction to Solid-State Electronic Devices (A+)

Introduction to Integrated Circuit Design (A+)

Other Courses

Data Structure (A+) Electromagnetic Waves (A+) Feedback Control Systems (A+) Computer Architecture (A+) Modern Physics (A+)

SKILL

GRE score 331/340 (Q:170/170, V:161/170)

TOEFL score 105/120 (R:29/30, L:29/30, S:22/30, W:25/30)

Software Languages C++, Matlab, and Python Hardware Languages Verilog, Hspice, and Laker

Simulation Tools COMSOL Multiphysics, and TCAD

SELECTED COURSE PROJECT

VLSI, Memory System Circuit Design Project

Jun. 2016

EE, NTHU

· Completed circuit design, pre-sim, layout, and post-sim of a memory system.

Semiconductor Microwave Electronic Devices, Term Paper $EE.\ NTHU$

Jun. 2016

· Investigated into silicon based RF semiconductor devices.